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(54) **Organic light emitting display device having an emission control driver for outputting emission control signals**

Organische lichtemittierende Anzeigevorrichtung mit einem Emissionssteuerungstreiber zur Ausgabe emissionssteuerender Signale

Dispositif d'affichage électroluminescent organique ayant un dispositif de contrôle d'émission générant des signaux de contrôle d'émission

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- **CHOI S M ET AL: "A SELF-COMPENSATED VOLTAGE PROGRAMMING PIXEL STRUCTURE FOR ACTIVE-MATRIX ORGANIC LIGHT EMITTING DIODES" IDW. PROCEEDINGS OF THE INTERNATIONAL DISPLAY WORKSHOPS, XX, XX, 2003, pages 535-538, XP008057381**

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Description**BACKGROUND OF THE INVENTION**

5 FIELD OF THE INVENTION

[0001] The present invention relates to an emission control driver and an organic light emitting display (OLED) device having the same and, more particularly, to a system-on-panel (SOP)-type emission control driver which generates signals to control emission of pixels and an OLED device having the same.

10 DISCUSSION OF THE BACKGROUND

[0002] Flat panel displays (FPDs) have been developed because they can be made smaller and lighter than display devices using cathode ray tubes (CRTs). In turn, FPD technology has given rise to liquid crystal displays (LCDs), field emission displays (FEDs), plasma display panels (PDPs), and organic light emitting displays (OLEDs). Among these FPDs, the PDP may have a large screen, but suffers from low luminance and poor luminous efficiency resulting in high power consumption. Moreover, the LCD has a relatively slow response speed and consumes a large quantity of power since it employs a backlight.

[0003] However, since the OLED makes use of an organic material to emit light, it has a wider viewing angle and faster response speed than the LCD. Also, the OLED is an emissive display that obtains good contrast and visibility. Further, the OLED consumes less power and can be made thin and lightweight because it needs no backlight.

20 **[0004]** Nevertheless, when the OLED is constructed to have a large screen, the dimensions of an electroluminescent (EL) panel used for a glass substrate with the OLED are limited by fabricating process limitations. Also, if the screen is too large, there is a greater probability of a defect occurring somewhere on the screen. Thus, a reduction in yield is unavoidable, and it is difficult to obtain uniformity across the screen.

[0005] As a solution to the above problems of the OLED, a tiling technique has been developed. In the tiling technique, 25 a plurality of EL panels are bonded together like tiles to form a single panel.

[0006] Each of the EL panels includes a plurality of pixels to display a predetermined image similar to a conventional OLED. In each of the EL panels, a scan driver applies a scan signal for enabling the pixels, and a data driver applies a data signal to a selected pixel. Also, an emission control driver applies an emission control signal to each of the pixels in order to control the exact programming of the data signal and the time required for an emission operation.

30 **[0007]** As described above, the scan driver, the data driver, and the emission control driver, which transmit various signals to drive the EL panels, may be electrically connected to each of the EL panels in various manners.

[0008] For example, the scan driver, the data driver, and the emission control driver may be mounted as chips on a tape carrier package (TCP) that is bonded and electrically connected to each of the EL panels. Alternatively, the drivers may be mounted as chips on a flexible printed circuit (FPC) or a film that is bonded and electrically connected to each 35 of the EL panels. The latter technique is referred to as a chip-on-flexible board (or chip-on-film) (COF) technique. In another method, the drivers are directly mounted on a glass substrate of the EL panel. This method is referred to as a chip-on-glass (COG) technique. These methods are costly and complicate the modules because the drivers should be separately designed and electrically connected to one another.

[0009] To overcome these drawbacks, a system-on-panel (SOP) technique has been recently developed. Also, there 40 have been attempts at designing a pixel portion, scan and emission control drivers, and/or a data driver in each EL panel, for constructing all systems in the EL panels.

[0010] In the OLED using the tiling technique, when each EL panel is formed as an SOP type, it is easy to bond the EL panels to one another. The SOP technique reduces the area of the drivers, in addition to the cost and labor associated with designing integrated circuits (ICs) for the drivers.

45 **[0011]** However, in order to develop the SOP-type OLED, it is necessary to consider many internal circumstances and conditions of the EL panels, such as a driving frequency and electron mobility of the data driver and/or the scan and emission control drivers. It is currently still difficult to design the data driver within a panel because the data driver needs a high driving frequency.

[0012] Accordingly, the data driver is formed as an IC using complementary metal oxide semiconductor (CMOS) 50 technology and connected to the EL panel, while the scan driver and/or the emission control driver are formed within the EL panel.

[0013] Therefore, there is a need for a simple circuit construction in which a SOP-type scan driver and emission control driver can be optimally driven within the EL panel.

SUMMARY OF THE INVENTION

55 **[0014]** Embodiments of the invention provide an emission control driver which is designed as a system-on-panel (SOP) type in an electroluminescent (EL) panel and generates emission signals to control the emission of pixels for an organic light emitting display (OLED) device.

[0015] Additional features of the invention will be set forth in the description which follows, and in part will be apparent

from the description, or may be learned by practice of the invention.

[0016] According to a first aspect of the invention, there is provided an organic light emitting display (OLED) device as set out in Claim 1. Preferred features of this aspect of the invention are set out in Claims 2 to 17.

[0017] It is to be understood that both the foregoing general description and the following detailed description are exemplary and explanatory and are intended to provide further explanation of the invention as claimed.

BRIEF DESCRIPTION OF THE DRAWINGS

[0018] Embodiments of the invention will now be described by way of example and with reference to the accompanying drawings in which:

[0019] FIG. 1 is a block diagram of an organic light emitting display (OLED) device using a tiling technique according to an exemplary embodiment of the present invention;

[0020] FIG. 2 is a detailed block diagram of an OLED array shown in FIG. 1;

[0021] FIG. 3 is a circuit diagram of a pixel of a pixel portion shown in FIG. 2;

[0022] FIG. 4 is a timing diagram illustrating the operation of a pixel circuit shown in FIG. 3;

[0023] FIG. 5 is a block diagram of an emission control driver of an organic EL panel according to the exemplary embodiment of the present invention;

[0024] FIG. 6 is a circuit diagram of a flip-flop of a shift register of the emission control driver shown in FIG. 5;

[0025] FIG. 7 is a detailed circuit diagram of an inverter of the flip-flop shown in FIG. 6;

[0026] FIG. 8 is a detailed circuit diagram of a logic gate of a logical operation portion of the emission control driver shown in FIG. 5; and

[0027] FIG. 9 is a timing diagram illustrating the operation of an emission control driver according to the exemplary embodiment of the present invention.

DETAILED DESCRIPTION OF THE ILLUSTRATED EMBODIMENTS

[0028] Embodiments of the invention are described more fully hereinafter with reference to the accompanying drawings. This invention may, however, be embodied in many different forms and should not be construed as limited to the exemplary embodiments set forth herein. Rather, these exemplary embodiments are provided so that this disclosure is thorough, and will fully convey the scope of the invention to those skilled in the art. In the drawings, the size and relative sizes of layers and regions may be exaggerated for clarity. Like reference numerals in the drawings denote like elements.

[0029] It will be understood that when an element such as a layer, film, region or substrate is referred to as being "on" another element, it can be directly on the other element or intervening elements may also be present. In contrast, when an element is referred to as being "directly on" another element, there are no intervening elements present.

[0030] FIG. 1 is a block diagram of an organic light emitting display (OLED) device using a tiling technique according to an exemplary embodiment of the present invention.

[0031] Referring to FIG. 1, the OLED device, which may be designed to various sizes, is formed by bonding a plurality of OLED arrays 100. FIG. 1, illustrates eight OLED arrays 100, which are disposed in two rows and four columns and are bonded to one another.

[0032] Each of the OLED arrays 100 includes an electroluminescent (EL) panel 10, which displays a predetermined image, and a data driver 20, which supplies a data signal to the EL panel 10.

[0033] The EL panels 10 each have a similar construction. The edges of the EL panels 10 are bonded to one another using an adhesive to form a combined EL panel. The adhesive may be an ultraviolet (UV)-curing resin or a thermal curing resin, for example, an epoxy resin.

[0034] Each of the EL panels 10 may be produced by the same fabricating process used for the production of an EL panel of a conventional OLED array. Accordingly, a large-sized EL panel may be fabricated by bonding a plurality of EL panels that are produced by the same fabricating process.

[0035] Each of the EL panels 10, as shown in FIG. 2, includes a scan driver (14); an emission control driver (16); and a plurality of pixels (18). Each of the drivers and pixels includes a thin film transistor (TFT) which has a polysilicon channel in order to obtain fast response speed and high uniformity. In this case, the polysilicon channel may be formed by forming an amorphous silicon (a-Si) layer on a glass substrate and crystallizing the a-Si layer using a low temperature polysilicon (LTPS) process.

[0036] A plurality of polysilicon TFTs may be formed using the LTPS process. Thereafter, the pixel portion, the scan driver, and the emission control driver may be formed using the transistors in each of the EL panels 10. The pixel portion is comprised of red (R), green (G), and blue (B) sub-pixels, and the scan and emission control drivers select respective pixels and generate signals for controlling an emission operation of the selected respective pixels. A detailed description of the EL panel 10 will be presented later.

[0037] Each data driver 20, as shown in FIG. 2, is designed as an external integrated circuit (IC) using complementary metal oxide semiconductor (CMOS) technology and electrically connected to the corresponding EL panel 10. The EL panel 10 is electrically connected to the data driver 20 using a metal pattern that is printed on a flexible film. That is, an

output terminal of the data driver 20 is electrically connected to one end of the metal pattern, and a data line disposed on the EL panel 10 is electrically connected to the other end thereof. This method is referred to as a tape carrier package (TCP) technique. Each of the data drivers 20 transmits a data signal to the pixel portion of the EL panel 10 through a plurality of conductive lines that are disposed on the flexible film.

[0038] FIG. 2 is a detailed block diagram of the OLED array shown in FIG. 1.

[0039] Referring to FIG. 2, the OLED array 100 includes an EL panel 10 and a data driver 20.

[0040] The EL panel 10 includes a pixel portion 12, a scan driver 14, and an emission control driver 16.

[0041] The pixel portion 12 includes a plurality of data lines D_1 - D_m , a plurality of scan lines S_1 - S_n , a plurality of emission control lines E_1 - E_n , and a plurality of pixel circuits P_{11} - P_{nm} (18), that are formed in regions where the data lines D_1 - D_m , the scan lines S_1 - S_n , and the emission control lines E_1 - E_n intersect one another.

[0042] The data lines D_1 - D_m are electrically connected to the data driver 20 and extend in a vertical direction. The data lines D_1 - D_m transmit data signals to the respective pixels P_{11} - P_{nm} .

[0043] Unlike a conventional OLED device, the scan lines S_1 - S_n and the emission control lines E_1 - E_n extend in the same direction as the data lines D_1 - D_m (i.e., in the vertical direction). However, each of the scan S_1 - S_n and emission E_1 - E_n control lines and includes a contact hole in order to transmit the same scan and emission control signals to the pixels arranged in a horizontal direction. Therefore, metal interconnections, which contact the scan S_1 - S_n and emission E_1 - E_n control lines through the contact holes, extend in a horizontal direction so that scan and emission control signals are transmitted to the pixels arranged in the horizontal direction.

[0044] Each of the pixels P_{11} - P_{nm} includes R, G, and B sub-pixels that are repeatedly arranged in rows and columns. The R, G, and B sub-pixels used for an organic emission layer to emit light are formed from different organic materials, but are otherwise similar to one another with respect to the interconnection layout and circuit connection of their respective driving circuits. Accordingly, each of the pixels P_{11} - P_{nm} emits R, G, or B light with luminance corresponding to a data signal applied thereto and combines the R, G, and B light to display a specific color. The circuit construction of each of the pixels P_{11} - P_{nm} will be described with reference to FIG. 3 and FIG. 4.

[0045] FIG. 3 is a circuit diagram for one of the pixels P_{11} - P_{nm} of the pixel portion shown in FIG. 2.

[0046] Referring to FIG. 3, a pixel circuit 18 includes a pixel driver 19 and an organic light emitting diode OLED.

[0047] The pixel driver 19 is connected to a data line D_m , a previous scan line S_{n-1} , a current scan line S_n , an emission control line E_n , a first power supply voltage line VDD, and a second power supply voltage line V_{SUS} . The pixel driver 19 receives a data signal V_{DATA} from the data line D_m and supplies a driving current I_{OLED} corresponding to the data signal V_{DATA} to the organic light emitting diode OLED.

[0048] The organic light emitting diode OLED includes an anode electrode, a cathode electrode, and an organic emission layer. The anode electrode is connected to the pixel driver 19, and the cathode electrode is connected to a reference power supply voltage line VSS. The organic light emitting diode OLED receives the driving current from the pixel driver 19 and emits light at a luminance corresponding to the amount of driving current I_{OLED} .

[0049] The pixel driver 19 includes five transistors M1-M5 and two capacitors C_{st} and C_{vth} . The configuration of the pixel driver 19 will now be described.

[0050] The switching transistor M4 has a source terminal connected to the data line D_m , and a gate terminal connected to the current scan line S_n . The switching transistor M4 is turned on in response to a scan signal applied from the scan line S_n and transmits the data signal V_{DATA} applied from the data line D_m .

[0051] The driving transistor M1 has a source terminal connected to the first power supply voltage line VDD and generates a driving current I_{OLED} corresponding to a voltage applied to a gate terminal thereof.

[0052] The threshold voltage compensation transistor M2 is connected between the gate terminal and a drain terminal of the driving transistor M1. The threshold voltage compensation transistor M2 is turned on in response to a previous scan signal transmitted via the previous scan line S_{n-1} , and compensates a threshold voltage V_{TH} of the driving transistor M1.

[0053] The first capacitor C_{vth} is connected between a drain terminal of the switching transistor M4 and the gate terminal of the driving transistor M1. The first capacitor C_{vth} stores a voltage corresponding to the threshold voltage V_{TH} of the driving transistor M1.

[0054] The second capacitor C_{st} is connected between the first power supply voltage line VDD and one terminal of the first capacitor C_{vth} and stores a data voltage V_{DATA} transmitted from the data line D_m .

[0055] The second power supply voltage application transistor M3 has a source terminal connected to the second power supply voltage line V_{SUS} , and a drain terminal connected to a connection point between the first and second capacitors C_{vth} and C_{st} . The second power supply voltage application transistor M3 is turned on in response to the previous scan signal S_{n-1} applied to a gate terminal thereof, thus the second power supply voltage V_{SUS} is applied to the connection point between the first and second capacitors C_{vth} and C_{st} .

[0056] The emission control transistor M5 is connected between the drain terminal of the driving transistor M1 and the anode electrode of the organic light emitting diode OLED. The emission control transistor M5 is turned on/off in response to an emission control signal E_n applied to a gate terminal thereof, so that the driving current I_{OLED} from the

driving transistor M1 is supplied to the organic light emitting diode OLED or cut off.

[0057] Hereinafter, the operation of the pixel circuit 18 will be described with reference to FIG. 4.

[0058] FIG. 4 is a timing diagram illustrating the operation of the pixel circuit shown in FIG. 3.

[0059] Referring to FIG. 3 and FIG. 4, first, once a low-level previous scan signal S_{n-1} , a high-level current scan signal S_n , and a high-level emission control signal E_n are applied to the pixel circuit 18, the threshold voltage compensation transistor M2 and the second power supply voltage application transistor M3 are turned on, and the other transistors M4 and M5 are turned off. Thus, the driving transistor M1 is diode-connected so that a voltage of $V_{DD} - |V_{TH}|$ is applied to one electrode B of the first capacitor C_{vth} . Also, the second power supply voltage application transistor M3 is turned on so that a voltage of V_{SUS} is applied to the other electrode A of the first capacitor C_{vth} . Accordingly, the first capacitor C_{vth} stores a voltage difference of $V_{SUS} - V_{DD} + |V_{TH}|$.

[0060] Thereafter, a low-level current scan signal S_n , a high-level previous scan signal S_{n-1} , and a high-level emission control signal E_n are applied to the pixel circuit 18, thus only the switching transistor M4 is turned on. In this case, the data voltage V_{DATA} is transmitted from the data line D_m through the switching transistor M4 to the other electrode A of the first capacitor C_{vth} . Thus, the other electrode A of the first capacitor C_{vth} has a voltage variation $\Delta V = V_{SUS} - V_{DATA}$, and the one electrode B of the first capacitor C_{vth} also has the same voltage variation as the other electrode A thereof. As a result, a voltage applied to the one electrode B of the first capacitor C_{vth} and the gate terminal of the driving transistor M1 is $V_{DD} - |V_{TH}| - \Delta V = V_{DD} - |V_{TH}| - V_{SUS} + V_{DATA}$.

[0061] Finally, a high-level previous scan signal S_{n-1} , a high-level current scan signal S_n , and a low-level emission control signal E_n are applied to the pixel circuit 18, thus only the emission control transistor M5 is turned on. In this case, the driving current I_{OLED} supplied from the driving transistor M1 can be expressed as shown in Equation 1:

[0062]

$$I_{OLED} = k(V_{gs} - |V_{th}|)^2 = k\{V_{DD} - (V_{DD} - |V_{th}| - V_{sus} + V_{data}) - |V_{th}|\}^2 \quad (1),$$

$$= k(V_{data} - V_{sus})^2,$$

[0063] where $|V_{TH}|$ refers to an absolute value of a threshold voltage of the driving transistor M1, and k is a constant.

[0064] As can be seen from Equation 1, the pixel circuit 18 shown in FIG. 3 can compensate the threshold voltage V_{TH} caused by the first power supply voltage VDD.

[0065] Referring to FIG. 2 again, the scan driver 14 is disposed between the data driver 20 and the pixel portion 12. Since a large-sized panel is formed by bonding a plurality of EL panels 10, the scan driver 14 should be formed on the same side as the data driver 20. The scan driver 14 is connected to a plurality of scan lines S_1 - S_n . Thus, the scan driver 14 sequentially transmits scan signals to the pixel portion 12 and sequentially selects each of the pixels P_{11} - P_{nm} .

[0066] The emission control driver 16 is disposed between the scan driver 14 and the pixel portion 12, and connected to a plurality of emission control lines E_1 - E_n . Thus, the emission control driver 16 sequentially transmits emission control signals to the pixel portion 12 and controls an emission time of each of the pixels P_{11} - P_{nm} .

[0067] The data driver 20 transmits a data signal to the pixel portion 12 of the EL panel 10 through a plurality of conductive lines disposed on the flexible film as described above.

[0068] According to the present invention as described above, the OLED array 100 includes the EL panel 10 and the data driver 20, where the EL panel 10 includes the pixel portion 12, the scan driver 14, and the emission control driver 16. Hereinafter, the structure and operation of the emission control driver 16 will be described in detail with reference to exemplary embodiments of the present invention.

[0069] FIG. 5 is a block diagram of an emission control driver of an organic EL panel according to the exemplary embodiment of the present invention.

[0070] Referring to FIG. 5, the emission control driver 16 includes a shift register 17 and a logical operation portion 22. The shift register 17 is connected to a plurality of flip-flops FF1, FF2, FF3, FF4,...shifting an input signal by one clock cycle and outputting the shifted signal. The logical operation portion 22 includes a plurality of logic gates OR1, OR2, OR3,...which receive output signals from the adjacent flip-flops FF1, FF2, FF3, and FF4 and generate emission control signals through logical OR operations for the received signals.

[0071] The first flip-flop FF1 receives a start pulse V_{SP} , a clock signal V_{CLK} , and an inverted clock signal V_{CLKB} , samples the start pulse V_{SP} at a falling edge of the clock signal V_{CLK} and maintains the sampled signal for a clock cycle, and outputs an output signal OUT 1 and an inverted output signal OUTB1.

[0072] The second flip-flop FF2 receives the output signal OUT1 of the first flip-flop FF1, the clock signal V_{CLK} , and the inverted clock signal V_{CLKB} , shifts the received signal for one cycle of the clock signal V_{CLK} , samples the shifted signal at a falling edge of the next cycle of the clock signal V_{CLK} and maintains the sampled signal for a clock cycle, and outputs an output signal OUT2 and an inverted output signal OUTB2.

[0073] Thereafter, the third, fourth,...flip-flops FF3, FF4,...perform the same operations as the first and second flip-flops FF1 and FF2 and output shifted signals. The flip-flops FF1, FF2, FF3, FF4,... may have the same construction, which will be described in detail later.

[0074] The logical operation portion 22 includes a plurality of logic gates OR1, OR2, OR3,...each of which is connected to an emission control line and transmits an emission control signal to each of the pixels.

[0075] The first logic gate OR1 receives the output signals OUT1 and OUTB1 from the first flip-flop FF1 and the output signals OUT2 and OUTB2 from the second flip-flop FF2. The first logic gate OR1 performs a logical OR operation on the output signals OUT1, OUTB1, OUT2, and OUTB2. Unlike a typical logic gate, the first logic gate OR1 of the present invention outputs a low-level emission control signal E_1 , only when the output signals OUT1 and OUT2 of the first and second flip-flops FF1 and FF2, respectively, are at low levels and the inverted output signals OUTB1 and OUTB2 of the first and second flip-flops FF1 and FF2, respectively, are at high levels; and outputs a high-level emission control signal E_1 in all other cases..

[0076] Next, the second logic gate OR2 receives the output signals OUT2 and OUTB2 of the second flip-flop FF2 and output signals OUT3 and OUTB3 of the third flip-flop FF3, performs the same logical OR operation as the first logic gate OR1, and outputs a second emission control signal E_2 .

[0077] Like the first and second logic gates OR1 and OR2, each of the third logic gate OR3 through an n-th logic gate ORn performs a logical OR operation for four input signals, and outputs each of emission control signals E_3 - E_n . The logic gates OR1 through ORn may have the same construction, which will be described in detail later.

[0078] As described above, the emission control driver of the present invention includes the shift register 17 and the logical operation portion 22, and a connection of the two flip-flops FF1 and FF2 adjacent to the shift register 17 with the single logic gate OR1 of the logical operation portion 22 is defined as a basic emission control driving circuit 16_1, which generates the emission control signal E_1 . The foregoing operating principle of the emission control driver shown in FIG. 5 will be described in detail later with reference to a timing diagram.

[0079] FIG. 6 is a circuit diagram of a representative flip-flop (i.e., the first flip-flop FF1) of the shift register of the emission control driver shown in FIG. 5.

[0080] Referring to FIG. 6, the flip-flop FF1 includes two switching transistors M6 and M7 and two inverters INV1 and INV2. More specifically, the flip-flop FF 1 is controlled by an inverted clock signal CLKB and includes the transistors M6 and M7 and the first and second inverters INV1 and INV2. The transistor M6 samples an input signal IN at a falling edge of the inverted clock signal CLKB, and the first inverter INV1 inverts an output signal of the transistor M6. The transistor M7 samples an output signal of the first inverter INV1 at a falling edge of a clock signal CLK, and the second inverter INV2 inverts an output signal of the transistor M7. Here, the transistors M6 and M7 are positive channel metal oxide semiconductors (PMOS) transistors.

[0081] Accordingly, when an input signal IN is applied to the transistor M6 and the inverted clock signal CLKB makes a high-to-low transition, the transistor M6 samples the input signal IN and transmits the sampled signal to the first inverter INV1. In response to a falling edge of the clock signal CLK, the transistor M7 is turned on, and the first inverter INV1 inverts the sampled signal and outputs the inverted signal. An output signal OUTB of the first inverter INV1 is transmitted from the transistor M7, inverted again by the second inverter INV2, and output as an output signal OUT.

[0082] As described above, the flip-flop FF1 according to the present invention makes use of the input signal IN, the clock signal CLK, and the inverted clock signal CLKB to generate a desired output signal. The input signal OUTB₁ and output signal OUT₁ of the second inverter INV2 are input as two input signals of the foregoing logic gate OR1. Also, the output signal OUT of the second inverter INV2 is input to the next flip-flop FF2, and the next flip-flop FF2 makes use of the input signal OUT1, the clock signal CLK, and the inverted clock signal CLKB shifted by a clock cycle, to generate a desired output signal OUT2 and OUTB2, and then OUT1, OUT2, OUTB1 and OUTB2 input as an input signal of the logic gate OR1. Accordingly, the input signals OUT1, OUT2, OUTB1 and OUTB2 of logic gate OR1 is selected from the flip-flop FF1 and FF2 without additional signals, so that power consumption may be reduced.

[0083] Hereinafter, the construction of the first and second inverters INV1 and INV2 used for the flip-flop FF1 will be described.

[0084] FIG. 7 is a detailed circuit diagram of an inverter of the flip-flop shown in FIG. 6.

[0085] Since the first and second inverters INV1 and INV2 have the same construction, only the construction of the first inverter INV1 will be described for convenience.

[0086] Referring to FIG. 7, the inverter INV1 includes three PMOS transistors M8, M9, and M10.

[0087] The transistor M8 has a source terminal connected to a first power supply voltage VDD, a gate terminal connected to an output terminal of the transistor M6 of the flip-flop FF1, and a drain terminal connected to an output terminal "out". The output terminal "out" is connected to an input terminal of the transistor M7 of the flip-flop FF1. Accordingly, the transistor M8 is turned on/off in response to an input signal "in" transmitted from the transistor M6 and outputs the first power supply voltage VDD to the output terminal "out" or cuts off the first power supply voltage VDD. Here, the first power supply voltage VDD is a positive power supply voltage, for example, 5 V.

[0088] The transistor M9 has a source terminal connected to the drain terminal of the transistor M8 and the output

terminal "out", and a drain terminal connected to a second power supply voltage VSS. Thus, the transistor M9 acts as an active load according to a voltage applied to a gate terminal thereof.

[0089] Also, the transistor M10 is connected between the gate and drain terminals of the transistor M9, has a gate terminal and a drain terminal, which are diode-connected, and controls a gate voltage of the transistor M9. Here, the second power supply voltage VSS is a negative power supply voltage, for example, -7 V. Accordingly, the transistor M9 acts as an active load and always remains turned on according to a difference between a voltage applied to the source terminal and a voltage applied to the gate terminal. Preferably, a channel width over a channel length W/L of the transistor M9 is smaller than that of the transistor M8. In this case, when the transistor M8 is turned on, turned-on resistance of the transistor M9 may be higher than that of the transistor M8.

[0090] Furthermore, the inverter INV1 may further include a capacitor C_{gs} , which is connected between the source and gate terminals of the transistor M9 and maintains a voltage V_{gs} between the source and gate terminals of the transistor M9 when the transistor M10 is turned off.

[0091] The operating principle of the above-described inverter INV1 will now be explained.

[0092] First, when an input signal of low-level (-7 V) "in" is applied to the gate terminal of the transistor M8, the transistor M8 is turned on, and the transistors M9 and M10 are also turned on. However, since the transistor M9 has a higher on-resistance than the transistor M8, a voltage at the output terminal "out" substantially becomes the first power supply voltage VDD, i.e., a high-level voltage of 5 V.

[0093] Next, once an input signal of high-level (5 V) "in" is applied to the gate terminal of the transistor M8, the transistor M8 is turned off, and the transistors M9 and M10 remain turned on. Thus, a voltage at the output terminal "out" is gradually transitioned from the high-level voltage of 5 V to a low level. In this case, the transistor M10 is turned off so that the output terminal "out" has low level. Accordingly, a voltage V_{gs} between the source and gate terminals of the transistor M9 is maintained at a constant level, and a voltage at the output terminal "out" connected to the source terminal of the transistor M9 makes a downward transition to the second power supply voltage VSS, i.e., a low-level voltage of -7 V. In this case, as the voltage at the output terminal "out" decreases, the gate voltage of the transistor M9 also makes a transition to -7 to -15 V.

[0094] As described above, the flip-flop of the present invention can sample an input signal and output a desired output signal in response to variations in the levels of a clock signal CLK and an inverted clock signal CLKB. Thus, output signals OUT1, OUTB1, OUT2, and OUTB2 of the adjacent flip-flops FF1 and FF2 are transmitted to input terminals of the logic gate OR1.

[0095] Hereinafter, the logic gate OR1 to which the output signals OUT1, OUTB1, OUT2, and OUTB2 of the adjacent flip-flops FF1 and FF2 are applied will be described in detail.

[0096] FIG. 8 is a detailed circuit diagram of one of a plurality of logic gates of the logical operation portion of the emission control driver shown in FIG. 5.

[0097] Referring to FIG. 8, the logic gate includes an input portion 31, a first active load 32, an output transistor M18, and a second active load 33. The input portion 31 is turned on/off in response to two input signals IN1 and IN2. The first active load 32 has a transistor M13 which is connected to the input portion 31 and selectively diode-connected in response to two inverted input signals INB1 and INB2. The output transistor M18 receives an output signal of the input portion 31 and is turned on/off in response to the level of the input signal. The second active load 33 has a transistor M17 which is connected to the output transistor M18 and selectively diode-connected in response to the two input signals IN1 and IN2.

[0098] Also, the logic gate further includes a switching portion 34, a first capacitor C1, and a second capacitor C2. The switching portion 34 is turned on/off in response to the input signals IN1 and IN2 and turns off the transistor M13 when the input signals IN1 and IN2 are at low levels. The first capacitor C1 maintains a voltage between a source terminal and a gate terminal of the transistor M13, and the second capacitor C2 maintains a voltage between a source terminal and a gate terminal of the transistor M17.

[0099] Further, the logic gate further includes a transistor M19 connected to both ends of the second capacitor C2. The transistor M19 is turned on/off in response to an output signal of the input portion 31 and turns off the transistor M17 when the output signal is at a high level.

[0100] Here, an input signal IN1 and an inverted input signal INB1 respectively correspond to an output signal OUT1 and an inverted output signal OUTB1 of the flip-flop FF1, and an input signal IN2 and an inverted input signal INB2 respectively correspond to an output signal OUT2 and an inverted output signal OUTB2 of the flip-flop FF2.

[0101] Specifically, the input portion 31 includes a transistor M11 and a transistor M12. The transistor M11 is connected to a positive power supply voltage V_{POS} and turned on/off according to the level of the input signal IN1. The transistor M12 is connected to the transistor M11 and turned on/off according to the level of the input signal IN2. Thus, the input portion 31 is turned on only when both the input signals IN1 and IN2 are at low levels and outputs the positive power supply voltage V_{POS} , and turned off in all other cases..

[0102] The first active load 32 includes a transistor M13 and a pair of transistors M15_1 and M15_2. The transistor M13 is connected between the transistor M12 and a negative power supply voltage V_{neg} and diode-connected according to the level of the inverted input signals INB1 and INB2. Each of the transistors M15_1 and M15_2 is connected between

a gate terminal and a drain terminal of the transistor M13 and turned on/off according to the level of the inverted input signals INB1 and INB2. Accordingly, the transistor M13 is diode-connected except in the case where both the input signals INB1 and INB2 are at high levels and applies a voltage corresponding to the sum of the negative power supply voltage V_{neg} and a threshold voltage V_{THM13} to an output terminal of the input portion 31.

[0103] The output transistor M18 is connected between the positive power supply voltage V_{POS} and an emission control line E1 and has a gate terminal connected to output terminals of the input portion 31 and the first active load 32 so that it is turned on/off in response to a voltage applied to the gate terminal. Thus, when the voltage applied to the gate terminal is at a low level, the transistor M18 is turned on and transmits the positive power supply voltage V_{POS} to the emission control line E1.

[0104] The second active load 33 includes a transistor M17 and a pair of transistors M16_1 and M16_2. The transistor M17 is connected between the transistor M18 and the negative power supply voltage V_{neg} and diode-connected according to the level of the input signals IN1 and IN2. Each of the transistors M16_1 and M16_2 is connected between a gate terminal and a drain terminal of the transistor M17 and turned on/off according to the level of the input signals IN1 and IN2. Thus, only when both the input signals IN1 and IN2 are at low levels, the transistor M17 is diode-connected and transmits a voltage corresponding to the sum of the negative power supply voltage V_{neg} and absolute value of a threshold voltage V_{THM17} to the emission control line E1.

[0105] Also, the switching portion 34 includes two transistors M14_1 and M14_2, which are connected in series. Each of the transistors M14_1 and M14_2 is connected between the source and gate terminals of the transistor M13 of the first active load 32 and turned on/off in response to the input signals IN1 and IN2. When both the input signals IN1 and IN2 are at low levels, the switching portion 34 drives a voltage difference V_{gsM13} between the source and gate terminals of the transistor M13 to 0 V so that the transistor M13 is turned off. Accordingly, when the input portion 31 is turned on, the flow of static current through the first active load 32 can be prevented.

[0106] Further, the transistor M19 is connected between the source and gate terminals of the transistor M17 of the second active load 33 and turned on/off in response to the output signal of the first input portion 31. Thus, when the output signal of the first input portion 31 is at a low level, the transistor M19 drives a voltage difference V_{gsM17} between the source and gate terminals of the transistor M17 to 0 V so that the transistor M17 is turned off. Accordingly, when the transistor M18 is turned on, the flow of static current through the second active load 33 can be prevented.

[0107] Here, all transistors of the logic gate are PMOS transistors. But, it would be apparent to those skilled in the art that all transistors of the logic gate may be negative channel metal oxide semiconductor (NMOS) transistors. That is, by replacing the PMOS transistors with NMOS transistors and changing the positive power supply voltage V_{POS} to the negative power supply voltage V_{neg} , a logic gate comprised of NMOS transistors may be designed.

[0108] The emission control signal E1 is output from the above-described logic gate according to the levels of the input signals IN1 and IN2 and the inverted input signals INB1 and INB2 as will be explained now.

[0109] First, when both the input signals IN1 and IN2 are at low levels and both the inverted input signals INB1 and INB2 are at high levels, both the transistors M11 and M12 of the input portion 31 are turned on, and both the transistors M14_1 and M14_2 of the switching portion 34 are also turned on. Also, both the transistors M16_1 and M16_2 of the second active load 33 are turned on. But, the transistors M15_1 and M15_2 of the first active load 32 are turned off.

[0110] Accordingly, the positive power supply voltage V_{POS} is transmitted from the input portion 31 to the gate terminals of the output transistor M18 and the transistor M19. In this case, the switching portion 34 is turned on and drives a source-gate voltage V_{gsM13} of the transistor M13 of the first active load 32 to 0 V. As a result, the transistor M13 is turned off, thus no static current flows in the first active load 32. Meanwhile, the output transistor M18 and the transistor M19 to which the positive power supply voltages V_{POS} are applied are turned off, and the transistor M17, which is diode-connected to the second active load 33, outputs an emission control signal at a low level corresponding to the sum of the negative power supply voltage V_{neg} and absolute value of the threshold voltage V_{THM17} .

[0111] Thereafter, when the input signal IN1 is at a high level and the input signal IN2 is at a low level or when the input signal IN1 is at a low level and the input signal IN2 is at a high level, the logic gate is in the following state.

[0112] Any one of the transistors M11 and M12 of the input portion 31 is turned off, and any one of the transistors M14_1 and M14_2 of the switching portion 34 is also turned off. Also, any one of the transistors M16_1 and M16_2 of the second active load 33 is turned off. But, any one of the parallel-connected transistors M15_1 and M15_2 of the first active load 32 is turned on.

[0113] Accordingly, the input portion 31 and the switching portion 34 are turned off, and the transistor M13 of the first active load 32 is diode-connected, thus a voltage at the gate terminal of the output transistor M18 is reduced to a low level corresponding to the sum of the negative power supply voltage V_{neg} and absolute value of the threshold voltage V_{THM13} . The output transistor M18 to which a low-level voltage is applied is turned on and applies the positive power supply voltage V_{POS} to the emission control line E1. In this case, the transistor M19 is turned on and drives the source-gate voltage V_{gsM17} of the transistor M17 of the second active load 33 to 0 V. Accordingly, the transistor M17 is turned off, thus no static current flows in the active load 33. As a result, a high-level signal that is equivalent to the positive power supply voltage V_{POS} is output to the emission control line E1.

[0114] Also, when both the input signals IN1 and IN2 are at high levels, the emission control signal E1 remains at a high level.

[0115] As described above, the logic gate of the logical operation portion 18 according to the present invention receives four signals OUT1, OUTB1, OUT2, and OUTB2 output from the adjacent flip-flops FF1 and FF2 without any additional signal and controls the first and second active loads 32 and 33 of the logic gate using the signals OUT1, OUTB1, OUT2, and OUTB2. Also, the logic gate of the logical operation portion 18 receives the output signals OUT1 and OUT2 and can generate a desired emission control signal E1 by performing a logical OR operation on the received signals OUT1 and OUT2. In this case, when the input signals IN1 and IN2 are at low levels, the flow of static current through the first and second active loads 32 and 33 can be prevented, and when the output signal of the input portion 31 is at a low level, the flow of static current through the second active load 33 can be prevented.

[0116] FIG. 9 is a timing diagram illustrating the operation of an emission control driver according to the exemplary embodiment of the present invention.

[0117] Referring to FIG. 9, a shift register having a plurality of flip-flops FF1-FFn+1 commonly receives a clock signal CLK and an inverted clock signal CLKB, and receives an output signal of a previous flip-flop as an input signal.

[0118] First, when a first flip-flop FF1 receives a start pulse SP, it outputs a high-level output signal OUT1 and a low-level inverted output signal OUTB1 for a clock cycle on a falling edge of a first cycle of the clock signal CLK.

[0119] Next, when a second flip-flop FF2 receives the output signal OUT1 of the first flip-flop FF1, it outputs a high-level output signal OUT2 and a low-level inverted output signal OUTB2 for a clock cycle on a falling edge of a second cycle of the clock signal CLK.

[0120] By repeating the above-described operation, finally, when an n+1-th flip-flop FFn+1 receives an output signal OUTn of an n-th flip-flop FFn, it outputs a high-level output signal OUTn+1 and a low-level inverted output signal OUTBn+1 for a clock cycle on a falling edge of an n+1-th cycle of the clock signal CLK.

[0121] In the above-described process, the shift register of the present invention outputs two signals OUT and OUTB that are shifted by one clock cycle.

[0122] Also, a logical operation portion having a plurality of logic gates OR1-ORn receives output signals of the flip-flops FF1-FFn+1, performs a logical OR operation on the received signals, and outputs an emission control signal.

[0123] First, the first logic gate OR1 receives two output signals OUT1 and OUTB1 from the first flip-flop FF1 and two output signals OUT2 and OUTB2 from the second flip-flop FF2. Thus, the first logic gate OR1 outputs a low-level emission control signal E1, only when the first and second output signals OUT1 and OUT2 are at low levels and the first and second inverted output signals OUTB1 and OUTB2 are at high levels, and outputs a high-level emission control signal E1 except for the above-described case.

[0124] Next, the second logic gate OR2 receives two output signals OUT2 and OUTB2 from the second flip-flop FF2 and two output signals OUT3 and OUTB3 from the third flip-flop FF3. Thus, the second logic gate OR2 outputs a low-level emission control signal E2, only when the second and third output signals OUT2 and OUT3 are at low levels and the second and third inverted output signals OUTB2 and OUTB3 are at high levels, and outputs a high-level emission control signal E2 except for the above-described case. The second emission control signal E2 is shifted by a clock cycle later than the first emission control signal E1 and output.

[0125] By repeating the above-described operation, finally, an n-th logic gate ORn receives two output signals OUTn and OUTBn from the n-th flip-flop FFn and receives two output signals OUTn+1 and OUTBn+1 from the n+1-th flip-flop FFn+1. Thus, the n-th logic gate ORn outputs a low-level emission control signal En, only when the n-th and n+1-th output signals OUTn and OUTn+1 are at low levels and the n-th and n+1-th inverted output signals OUTBn and OUTBn+1 are at high levels, and outputs a high-level emission control signal En except for the above-described case.

[0126] According to the present invention as described above, a system-on-panel (SOP)-type emission control driver for the OLED can be easily fabricated by directly forming a plurality of flip-flops and a plurality of logic gates within a panel using PMOS transistors.

[0127] Also, since each of the logic gates makes use of four output signals of adjacent flip-flops as input signals without any additional signal, power consumption can be reduced.

[0128] Furthermore, the present invention employs four-input logic gates so that static current generated by a low-level input signal can be cut off, thus reducing power consumption caused by leakage current.

[0129] Therefore, the present invention provides an optimal SOP-type emission control driver and an OLED device that can minimize power consumption.

[0130] It will be apparent to those skilled in the art that various modifications and variation can be made in the present invention without departing from the scope of the invention, which is as set out in the appended claims.

Claims

1. An organic light emitting display (OLED) device, comprising an electroluminescent panel (10), said electrolumines-

cent panel comprising:

a pixel portion having a plurality of pixels arranged to display an image;
 an emission control driver (16) arranged to apply an emission signal to control an emission time of each of the
 pixels, said emission control driver (16) being **characterized in that** it comprises:

a shift register (17) including a plurality of flip-flops, wherein the first flip-flop is adapted to receive a start pulse and the rest of the flip-flops are each adapted to receive an output signal of a previous flip-flop and each flip-flop generates an output signal and an inverted output signal in synchronization with a clock signal and an inverted clock signal; and

a logical operation portion (22) including a plurality of logic gates, wherein each of the logic gates is adapted to receive a first said output signal and a first said inverted output signal from one of two adjacent said flip-flops and to receive a second said output signal and a second said inverted output signal from the other of the two adjacent flip-flops, wherein each said logic gate is adapted to control an active load located within said logic gate, using the received output signals so as to prevent the flow of static current in said logic gate, and wherein each said logic gate is adapted to output an emission control signal through a logical operation on the first and second output and inverted output signals, wherein a low-level emission control signal is outputted when the first and second outputs are at low levels and the inverted output signals are at high levels and a high-level emission control signal is outputted in all other cases.

2. A device according to claim 1, wherein each of the flip-flops comprises:

a first transistor (M6); a first inverter (INV1);

a second transistor (M7); and

a second inverter (INV2),

wherein the first transistor (M6) is adapted to sample an input signal on a falling edge of the inverted clock signal; the first inverter (INV1) is adapted to invert an output signal of the first transistor (M6); the second transistor (M7) is adapted to sample an output signal of the first inverter (INV1) on a falling edge of the clock signal; and the second inverter (INV2) is adapted to invert an output signal of the second transistor (M7).

3. A device according to claim 2, wherein each of the adjacent flip-flops is adapted to transmit the output signal of the second transistor (M7) and an output signal of the second inverter (INV2) to a corresponding logic gate.

4. A device according to claim 2 or 3, wherein each of the first and second inverters comprises:

a third transistor (M8) connected between a positive power supply voltage and an output terminal and which is adapted to turn on/off in response to a signal transmitted through one of the first and second transistors (M6, M7) of the flip-flop; and

a fourth transistor (M9) connected between a negative power supply voltage and the output terminal and which is adapted to control the amount of current depending on the on/off operation of the third transistor (M8).

5. A device according to claim 4, wherein each of the first and second inverters (INV1, INV2) further comprises:

a fifth transistor (M10) connected between a gate terminal and a drain terminal of the fourth transistor (M9) and diode-connected to control a gate voltage of the fourth transistor (M9).

6. A device according to claim 5, wherein the third transistor (M8) has a lower turn-on resistance than the fourth transistor (M9).

7. A device according to claim 6, wherein each of the first and second inverters further comprises:

a capacitor (C_{gs}) connected between a source terminal and the gate terminal of the fourth transistor (M9) and which is adapted to maintain a voltage between the source and gate terminals of the fourth transistor (M9) when the fifth transistor (M10) is turned off.

8. A device according claim 7, wherein the first through fifth transistors (M6-M10) are positive channel metal oxide semiconductors (PMOS) transistors.

9. A device according to any preceding claim, wherein each of the logic gates comprises:

an input portion (31) connected to a first power supply voltage and which is adapted to turn on/off according to the levels of the first and second output signals of the said respective two adjacent flip-flops;
 a first active load (32), which includes a sixth transistor (M13) connected between the input portion (31) and a second power supply voltage and selectively diode-connected according to the levels of the first and second inverted output signals of the two adjacent flip-flops;
 an output transistor (M18) connected between the first power supply voltage and an emission control line and which is adapted to turn on/off according to the level of an output signal of one of the input portion (31) and the first active load (32); and
 a second active load (33), which has a seventh transistor (M17) connected between the second power supply voltage and the emission control line and selectively diode-connected according to the levels of the first and second output signals of the two adjacent flip-flops.

10. A device according to claim 9, wherein each input portion (31) comprises:

an eighth transistor (M11) connected to the first power supply voltage and which is adapted to turn on/off according to the level of the respective said first output signal; and
 a ninth transistor (M12) connected in series to the eighth transistor (M11) and which is adapted to turn on/off according to the level of the respective said second output signal.

11. A device according to claim 10, wherein the first active load comprises:

a tenth transistor (M15_1) connected between a gate terminal and a drain terminal of the sixth transistor (M13) and which is adapted to turn on/off according to the level of the first inverted output signal; and
 an eleventh transistor (M15_2) connected in parallel to the tenth transistor (M15_1) and which is adapted to turn on/off in response to the level of the second inverted output signal,
 wherein the arrangement is such that, when both the first and second inverted output signals are at high levels, the flow of current into the first active load (32) is cut off.

12. A device according to claim 11, wherein the second active load (33) comprises:

a twelfth transistor (M16_1) connected to a gate terminal of the seventh transistor (m17) and which is adapted to turn on/off according to the level of the first output signal; and
 a thirteenth transistor (m16_2) connected in series to the twelfth transistor (M16_1) and which is adapted to turn on/off according to the level of the second output signal,
 wherein the arrangement is such that, when at least one of the first and second output signals is at a high level, the flow of current into the second active load (33) is cut off.

13. A device according to claim 12, wherein each of the logic gates further comprises a switching portion (34) having:

a fourteenth transistor (M14_1) connected to a source terminal of the sixth transistor (M13) and which is adapted to turn on/off according to the level of the first output signal; and
 a fifteenth transistor (M14_2) connected in series to the fourteenth transistor (M14_1) and which is adapted to turn on/off according to the level of the second output signal,
 wherein the arrangement is such that, when both the first and second output signals are at low levels, the switching portion (34) turns off the first transistor (M6) so that the flow of current into the first active load (32) is cut off.

14. A device driver according to one of Claims 9 to 13, wherein each of the logic gates further comprises:

a first capacitor (C₁) connected between the source terminal and the gate terminal of the sixth transistor (M13) and which is adapted to maintain a voltage between the source and gate terminals of the sixth transistor (M13); and
 a second capacitor (C₂) connected between a source terminal and a gate terminal of the seventh transistor (M17) and which is adapted to maintain a voltage between the source and gate terminals of the seventh transistor (M17).

15. A device according to claim 14, wherein each of the logic gates further comprises a sixteenth transistor (M19) connected to both ends of the second capacitor (C₂) and which is adapted to turn on/off according to the level of the output signal of one of the input portion (31) and the first active load (32).

16. A device according to claim 15, wherein the sixth through sixteenth transistors are positive channel metal oxide semiconductors (PMOS) transistors.

17. A device according to Claim 16, wherein the OLED device is fabricated by combining a plurality of said OLED arrays using a tiling technique to display a predetermined image.

Patentansprüche

1. Organische lichtemittierende Anzeigeeinrichtung (OLED), eine Elektrolumineszenzplatte (10) umfassend, wobei die Elektrolumineszenzplatte umfasst:

einen Pixelteil mit einer Vielzahl von Pixeln, die zum Anzeigen eines Bildes angeordnet sind;
einen Emissionssteuertreiber (16), zum Anlegen eines Emissionssignals angeordnet, um eine Emissionszeit eines jeden der Pixel zu steuern, wobei der Emissionssteuertreiber (16) **dadurch gekennzeichnet ist, dass** er umfasst:

ein Schieberegister (17) mit einer Vielzahl von Flipflops, worin das erste Flipflop dazu angepasst ist, einen Startimpuls zu empfangen, und jedes der restlichen Flipflops dazu angepasst ist, ein Ausgangssignal eines vorherigen Flipflops zu empfangen, und jedes Flipflop ein Ausgangssignal und ein invertiertes Ausgangssignal synchron mit einem Taktsignal und einem invertierten Taktsignal erzeugt; und
einen Logikoperationsteil (22) mit einer Vielzahl von Logik-Gates, worin jedes der Logik-Gates dazu angepasst ist, ein erstes Ausgangssignal und ein erstes invertiertes Ausgangssignal von einem von zwei benachbarten Flipflops zu empfangen und ein zweites Ausgangssignal und ein zweites invertiertes Ausgangssignal vom anderen der zwei benachbarten Flipflops zu empfangen, worin jedes Logik-Gate dazu angepasst ist, eine innerhalb des Logik-Gates anliegende Wirklast unter Verwendung der empfangenen Ausgangssignale zu steuern, um den Fluss von Ruhestrom im Logik-Gate zu verhindern, und worin jedes Logik-Gate dazu angepasst ist, ein Emissionssteuersignal durch eine Logikoperation auf den ersten und zweiten Ausgangs- und invertierten Ausgangssignalen auszugeben, worin ein schwaches Emissionssteuersignal ausgegeben wird, wenn die ersten und zweiten Ausgaben schwach sind und die invertierten Ausgangssignale stark sind, und ein starkes Emissionssteuersignal in allen anderen Fällen ausgegeben wird.

2. Einrichtung nach Anspruch 1, worin jedes der Flipflops umfasst:

einen ersten Transistor (M6);
einen ersten Inverter (INV1);
einen zweiten Transistor (M7); und
einen zweiten Inverter (INV2);
worin der erste Transistor (M6) dazu angepasst ist, ein Eingangssignal auf einer fallenden Flanke des invertierten Taktsignals abzutasten; der erste Inverter (INV1) dazu angepasst ist, ein Ausgangssignals des ersten Transistors (M6) zu invertieren; der zweite Transistor (M7) dazu angepasst ist, ein Ausgangssignal des ersten Inverters (INV1) auf einer fallenden Flanke des Taktsignals abzutasten; und der zweite Inverter (INV2) dazu angepasst ist, ein Ausgangssignal des zweiten Transistors (M7) zu invertieren.

3. Einrichtung nach Anspruch 2, worin jedes der benachbarten Flipflops dazu angepasst ist, das Ausgangssignal des zweiten Transistors (M7) und ein Ausgangssignal des zweiten Inverters (INV2) an ein entsprechendes Logik-Gate zu übertragen.

4. Einrichtung nach Anspruch 2 oder 3, worin jeder der ersten und zweiten Inverter umfasst:

einen dritten Transistor (M8), der zwischen eine positive Energieversorgungsspannung und einen Ausgangsanschluss geschaltet ist und zum Ein-/Ausschalten angepasst ist als Antwort auf ein durch einen der ersten und zweiten Transistoren (M6, M7) des Flipflops übertragenes Signal; und
einen vierten Transistor (M9), der zwischen eine negative Energieversorgungsspannung und den Ausgangs-

anschluss geschaltet ist und der dazu angepasst ist, die Strommenge in Abhängigkeit von der Ein/Aus-Operation des dritten Transistors (M8) zu steuern.

5. Einrichtung nach Anspruch 4, worin jeder der ersten und zweiten Inverter (INV1, INV2) außerdem umfasst:

einen fünften Transistor (M10), der zwischen einen Gate-Anschluss und einen Drain-Anschluss des vierten Transistors (M9) geschaltet ist und als Diode geschaltet ist, um eine Gate-Spannung des vierten Transistors (M9) zu steuern.

6. Einrichtung nach Anspruch 5, worin der dritte Transistor (M8) einen niedrigeren Einschaltwiderstand hat als der vierte Transistor (M9).

7. Einrichtung nach Anspruch 6, worin jeder der ersten und zweiten Inverter außerdem umfasst:

einen Kondensator (C_{gs}), der zwischen einen Source-Anschluss und den Gate-Anschluss des vierten Transistors (M9) geschaltet ist und der dazu angepasst ist, eine Spannung zwischen den Source- und Gate-Anschlüssen des vierten Transistors (M9) aufrechtzuerhalten, wenn der fünfte Transistor (M10) ausgeschaltet ist.

8. Einrichtung nach Anspruch 7, worin die ersten bis fünften Transistoren (M6-M10) PMOS(Metalloxidhalbleiter mit positivem Kanal)-Transistoren sind.

9. Einrichtung nach einem vorhergehenden Anspruch, worin jedes der Logik-Gates umfasst:

einen Eingangsteil (31), der an eine erste Energieversorgungsspannung angeschlossen ist und der zum Ein-/Ausschalten angepasst ist gemäß den Pegeln der ersten und zweiten Ausgangssignale der jeweiligen zwei benachbarten Flipflops;

eine erste Wirklast (32), einen sechsten Transistor (M13) enthaltend, der zwischen den Eingangsteil (31) und eine zweite Energieversorgungsspannung geschaltet ist und selektiv als Diode geschaltet ist gemäß den Pegeln der ersten und zweiten invertierten Ausgangssignale der zwei benachbarten Flipflops;

einen Ausgangstransistor (M18), der zwischen die erste Energieversorgungsspannung und eine Emissionssteuerleitung geschaltet ist und der zum Ein-/Ausschalten angepasst ist gemäß dem Pegel eines Ausgangssignals von einem von Folgenden: dem Eingangsteil (31) und der ersten Wirklast (32); und

eine zweite Wirklast (33), die einen siebten Transistor (M17) hat, der zwischen die zweite Energieversorgungsspannung und die Emissionssteuerleitung geschaltet ist und selektiv als Diode geschaltet ist gemäß den Pegeln der ersten und zweiten Ausgangssignale der zwei benachbarten Flipflops.

10. Einrichtung nach Anspruch 9, worin jeder Eingangszeit (31) umfasst:

einen achten Transistor (M11), der an die erste Energieversorgungsspannung angeschlossen ist und der zum Ein-/Ausschalten angepasst ist gemäß dem Pegel des jeweiligen ersten Ausgangssignals; und
einen neunten Transistor (M12), der an den achten Transistor (M11) in Reihe geschaltet ist und der zum Ein-/Ausschalten angepasst ist gemäß dem Pegel des jeweiligen zweiten Ausgangssignals.

11. Einrichtung nach Anspruch 10, worin die erste Wirklast umfasst:

einen zehnten Transistor (M15_1), der zwischen einen Gate-Anschluss und einen Drain-Anschluss des sechsten Transistors (M13) geschaltet ist und der zum Ein-/Ausschalten angepasst ist gemäß dem Pegel des ersten invertierten Ausgangssignals; und

einen elften Transistor (M15_2), der mit dem zehnten Transistor (M15_1) parallel geschaltet ist und der zum Ein-/Ausschalten angepasst ist als Antwort auf den Pegel des zweiten invertierten Ausgangssignals, worin die Anordnung so ist, dass, wenn sowohl die ersten als auch die zweiten invertierten Ausgangssignale stark sind, der Stromfluss in die erste Wirklast (32) abgeschnitten wird.

12. Einrichtung nach Anspruch 11, worin die zweite Wirklast (33) umfasst:

einen zwölften Transistor (M16_1), der an einen Gate-Anschluss des siebten Transistors (M17) angeschlossen ist und der zum Ein-/Ausschalten angepasst ist gemäß dem Pegel des ersten Ausgangssignals; und
einen dreizehnten Transistor (M16_2), der mit dem zwölften Transistor (M16_1) in Reihe geschaltet ist und der

zum Ein-/Ausschalten angepasst ist gemäß dem Pegel des zweiten Ausgangssignals, worin die Anordnung so ist, dass, wenn mindestens eins der ersten und zweiten Ausgangssignale stark ist, der Stromfluss in die zweite Wirklast (33) abgeschnitten wird.

13. Einrichtung nach Anspruch 12, worin jedes der Logik-Gates außerdem einen Schaltteil (34) umfasst mit:

einem vierzehnten Transistor (M14_1), der an einen Source-Anschluss des sechsten Transistors (M13) angeschlossen ist und zum Ein-/Ausschalten angepasst ist gemäß dem Pegel des ersten Ausgangssignals; und einem fünfzehnten Transistor (M14_2), der mit dem vierzehnten Transistor (M14_1) in Reihe geschaltet ist und der zum Ein-/Ausschalten angepasst ist gemäß dem Pegel des zweiten Ausgangssignals, worin die Anordnung so ist, dass, wenn sowohl die ersten als auch die zweiten Ausgangssignale schwach sind, der Schaltteil (34) den ersten Transistor (M6) ausschaltet, sodass der Stromfluss in die erste Wirklast (32) abgeschnitten wird.

14. Einrichtungstreiber nach einem der Ansprüche 9 bis 13, worin jedes der Logik-Gates außerdem umfasst:

einen ersten Kondensator (C_1), der zwischen den Source-Anschluss und den Gate-Anschluss des sechsten Transistors (M13) geschaltet ist und der dazu angepasst ist, eine Spannung zwischen den Source- und Gate-Anschlüssen des sechsten Transistors (M13) aufrechtzuerhalten; und einen zweiten Kondensator (C_2), der zwischen einen Source-Anschluss und einen Gate-Anschluss des siebten Transistors (M17) geschaltet ist und der dazu angepasst ist, eine Spannung zwischen den Source- und Gate-Anschlüssen des siebten Transistors (M17) aufrechtzuerhalten.

15. Einrichtung nach Anspruch 14, worin jedes der Logik-Gates außerdem einen sechzehnten Transistor (M19) umfasst, der an beide Enden des zweiten Kondensators (C_2) angeschlossen ist und der zum Ein-/Ausschalten angepasst ist gemäß dem Pegel des Ausgangssignals von einem von Folgenden: dem Eingangsteil (31) und der ersten Wirklast (32).

16. Einrichtung nach Anspruch 15, worin die sechsten bis sechzehnten Transistoren PMOS(Metalloxidhalbleiter mit positivem Kanal)-Transistoren sind.

17. Einrichtung nach Anspruch 16, worin die OLED-Einrichtung durch Kombinieren einer Vielzahl der OLED-Arrays unter Verwendung einer Kacheltechnik hergestellt wird, um ein vorbestimmtes Bild anzuzeigen.

Revendications

1. Dispositif d'affichage électroluminescent organique (OLED), comportant un panneau électroluminescent (10), ledit panneau électroluminescent comportant:

une partie de pixels présentant une pluralité de pixels agencés de manière à afficher une image; un pilote de commande d'émission (16) agencé de manière à appliquer un signal d'émission pour commander une durée d'émission de chacun des pixels, ledit pilote de commande d'émission (16) étant **caractérisé en ce qu'il** comporte:

un registre à décalage (17) comportant une pluralité de bascules bistables, dans lequel la première bascule bistable est apte à recevoir une impulsion de départ et les bascules bistables restantes sont chacune aptes à recevoir un signal de sortie d'une bascule bistable précédente, et chaque bascule bistable génère un signal de sortie et un signal de sortie inversé en synchronisation avec un signal d'horloge et un signal d'horloge inversé; et

une partie d'opération logique (22) comportant une pluralité de grilles logiques, dans laquelle chacune des grilles logiques est apte à recevoir un dit premier signal de sortie et un dit premier signal de sortie inversé en provenance de l'une desdites deux bascules bistables adjacentes et à recevoir un dit second signal de sortie et un dit second signal de sortie inversé de l'autre des deux bascules bistables adjacentes, dans laquelle chaque dite grille logique est apte à commander une charge active localisée au sein de ladite grille logique, en utilisant les signaux de sortie reçus, de manière à empêcher le passage de courant statique dans ladite grille logique, et dans laquelle chaque dite grille logique est apte à générer en sortie un signal de commande d'émission par le biais d'une opération logique sur les premier et second signaux de sortie

et signaux de sortie inversés, dans lequel un signal de commande d'émission de faible niveau est généré en sortie lorsque les première et seconde sorties sont à des niveaux bas et que les signaux de sortie inversés sont à des niveaux élevés, et un signal de commande d'émission de haut niveau est généré en sortie dans tous les autres cas.

2. Dispositif selon la revendication 1, dans lequel chacune des bascules bistables comprend:

un premier transistor (M6);
un premier inverseur (INV1);
un deuxième transistor (M7); et
un second inverseur (INV2);

dans lequel le premier transistor (M6) est apte à échantillonner un signal d'entrée sur un front de descente du signal d'horloge inversé; le premier inverseur (INV1) est apte à inverser un signal de sortie du premier transistor (M6); le deuxième transistor (M7) est apte à échantillonner un signal de sortie du premier inverseur (INV1) sur un front de descente du signal d'horloge; et le second inverseur (INV2) est apte à inverser un signal de sortie du deuxième transistor (M7).

3. Dispositif selon la revendication 2, dans lequel chacune des bascules bistables adjacentes est apte à transmettre le signal de sortie du deuxième transistor (M7) et un signal de sortie du second inverseur (INV2) à une grille logique correspondante.

4. Dispositif selon la revendication 2 ou 3, dans lequel chacun des premier et second inverseurs comprend:

un troisième transistor (M8) connecté entre une tension d'alimentation positive et une borne de sortie, et lequel est apte à se mettre sous tension/hors tension en réponse à un signal émis par l'un des premier et deuxième transistors (M6, M7) de la bascule bistable; et

un quatrième transistor (M9) connecté entre une tension d'alimentation négative et la borne de sortie et qui est apte à commander la quantité de courant en fonction de l'opération de mise sous/hors tension du troisième transistor (M8).

5. Dispositif selon la revendication 4, dans lequel chacun des premier et second inverseurs (INV1, INV2) comprend en outre:

un cinquième transistor (M10) connecté entre une borne de grille et une borne de drain du quatrième transistor (M9) et connecté en diode pour commander une tension de grille du quatrième transistor (M9).

6. Dispositif selon la revendication 5, dans lequel le troisième transistor (M8) présente une résistance d'enclenchement inférieure à celle du quatrième transistor (M9).

7. Dispositif selon la revendication 6, dans lequel chacun des premier et second inverseurs comprend en outre:

un condensateur (C_{gs}) connecté entre une borne source et la borne de grille du quatrième transistor (M9) et lequel est apte à maintenir une tension entre la borne source et la borne de grille du quatrième transistor (M9) lorsque le cinquième transistor (M10) est mis hors tension.

8. Dispositif selon la revendication 7, dans lequel les premier à cinquième transistors (M6-M10) sont des transistors MOS à canal P (semi-conducteurs à oxyde de métal à canal positif, PMOS).

9. Dispositif selon l'une quelconque des revendications précédentes, dans lequel chacune des grilles logiques comprend:

une partie d'entrée (31) connectée à une première tension d'alimentation et laquelle est apte à se mettre sous/hors tension selon les niveaux des premier et second signaux de sortie desdites deux bascules bistables adjacentes respectives;

une première charge active (32), laquelle inclut un sixième transistor (M13) connecté entre la partie d'entrée (31) et une seconde tension d'alimentation et sélectivement connecté en diode selon les niveaux des premier et second signaux de sortie inversés des deux bascules bistables adjacentes;

un transistor de sortie (M18) connecté entre la première tension d'alimentation et une ligne de commande

d'émission et lequel est apte à se mettre hors/sous tension selon le niveau d'un signal de sortie de l'une parmi la partie d'entrée (31) et la première charge active (32); et
une seconde charge active (33), laquelle présente un septième transistor (M17) connecté entre la seconde tension d'alimentation et la ligne de commande d'émission et connecté en diode de manière sélective selon les niveaux des premier et second signaux de sortie des deux bascules bistables adjacentes.

10. Dispositif selon la revendication 9, dans lequel chaque partie d'entrée (31) comporte:

un huitième transistor (M11) connecté à la première tension d'alimentation et lequel est apte à se mettre hors/sous tension selon le niveau dudit premier signal de sortie respectif; et
un neuvième transistor (M12) connecté en série au huitième transistor (M11) et lequel est apte à se mettre hors/sous tension selon le niveau dudit second signal de sortie respectif.

11. Dispositif selon la revendication 10, dans lequel la première charge active comporte:

un dixième transistor (M15_1) connecté entre une borne de grille et une borne de drain du sixième transistor (M13) et lequel est apte à se mettre hors/sous tension selon le niveau du premier signal de sortie inversé;
une onzième transistor (M15_2) connecté en parallèle au dixième transistor (M15_1) et lequel est apte à se mettre hors/sous tension en réponse au niveau du second signal de sortie inversé;
dans lequel l'agencement est tel que, lorsque les premier et second signaux de sortie inversés sont à des niveaux élevés, le flux de courant dans la première charge active (32) est coupé.

12. Dispositif selon la revendication 11, dans lequel la seconde charge active (33) comporte:

un douzième transistor (M16_1) connecté à une borne de grille du septième transistor (M17) et lequel est apte à se mettre hors/sous tension selon le niveau du premier signal de sortie; et
un treizième transistor (M16_2) connecté en série au douzième transistor (M16_1) et lequel est apte à se mettre hors/sous tension selon le niveau du second signal de sortie;
dans lequel l'agencement est tel que, lorsqu'au moins un des premier et second signaux de sortie est à un niveau élevé, le flux de courant dans la seconde charge active (33) est coupé.

13. Dispositif selon la revendication 12, dans lequel chacune des grilles logiques comprend en outre une partie de commutation (34) comportant:

une quatorzième transistor (M14_1) connecté à une borne source du sixième transistor (M13) et lequel est apte à se mettre hors/sous tension selon le niveau du premier signal de sortie;
un quinzième transistor (M14_2) connecté en série au quatorzième transistor (M14_1) et lequel est apte à se mettre hors/sous tension selon le niveau du second signal de sortie;
dans lequel l'agencement est tel que, lorsque les premier et second signaux de sortie sont à des niveaux faibles, la partie de commutation (34) met hors tension le premier transistor (M6), de sorte que le flux de courant dans la première charge active (32) est coupé.

14. Pilote de dispositif selon l'une quelconque des revendications 9 à 13, dans lequel chacune des grilles logiques comprend en outre:

un premier condensateur (C_1) connecté entre la borne source et la borne de grille du sixième transistor (M13) et lequel est apte à maintenir une tension entre la borne source et la borne de grille du sixième transistor (M13); et
un second condensateur (C_2) connecté entre une borne source et une borne de grille du septième transistor (M17) et lequel est apte à maintenir une tension entre la borne source et la borne de grille du septième transistor (M17).

15. Dispositif selon la revendication 14, dans lequel chacune des grilles logiques comprend en outre un seizième transistor (M19) connecté aux deux extrémités du second condensateur (C_2) et lequel est apte à se mettre sous/hors tension selon le niveau du signal de sortie de l'une parmi la partie d'entrée (31) et la première charge active (32).

16. Dispositif selon la revendication 15, dans lequel les sixième à seizième transistors sont des transistors MOS à canal P (semi-conducteurs à oxyde de métal à canal positif, PMOS).

17. Dispositif selon la revendication 16, dans lequel le dispositif OLED est fabriqué en combinant une pluralité desdites matrices OLED en faisant appel à une technique de juxtaposition pour afficher une image prédéterminé.

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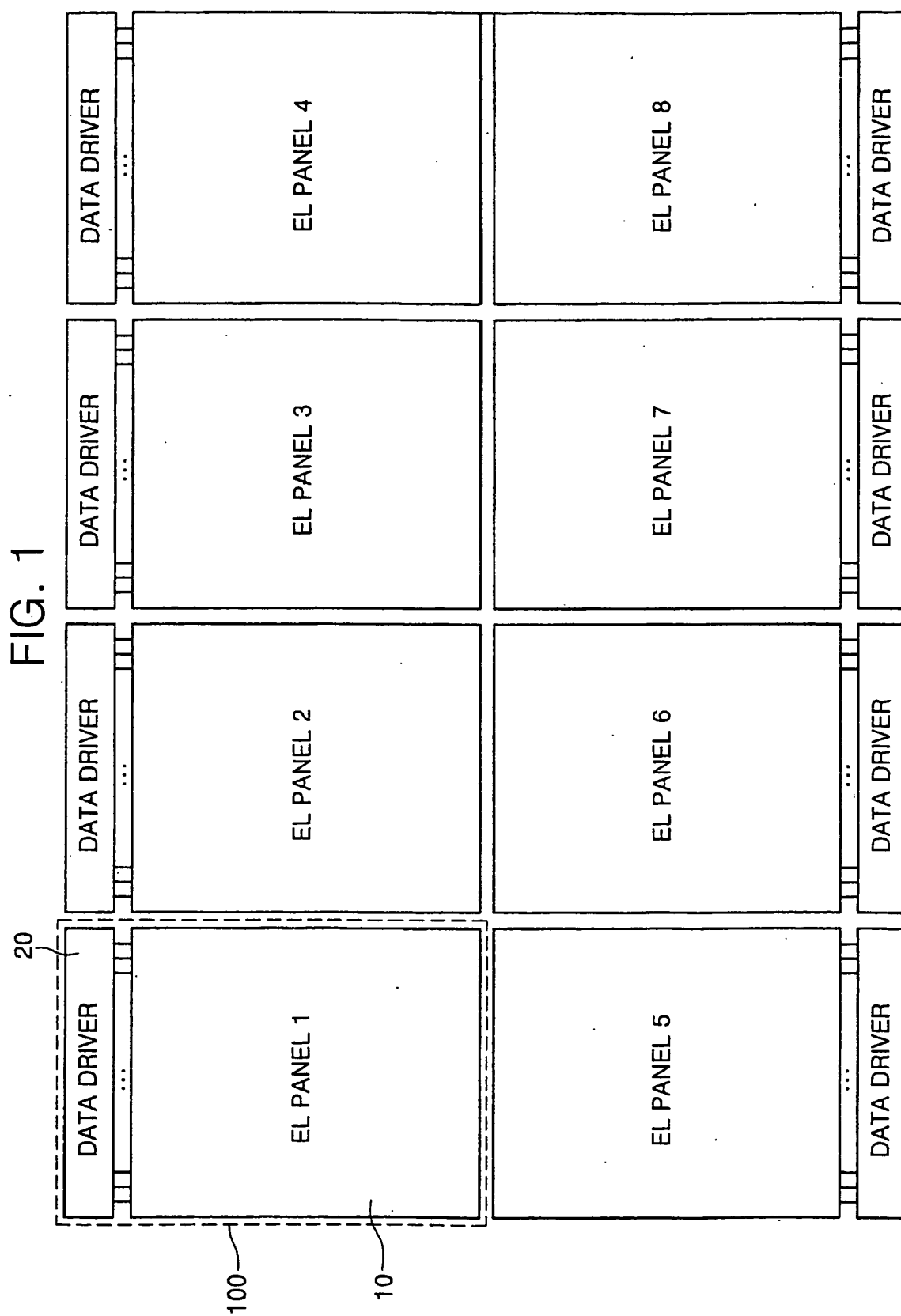


FIG. 2

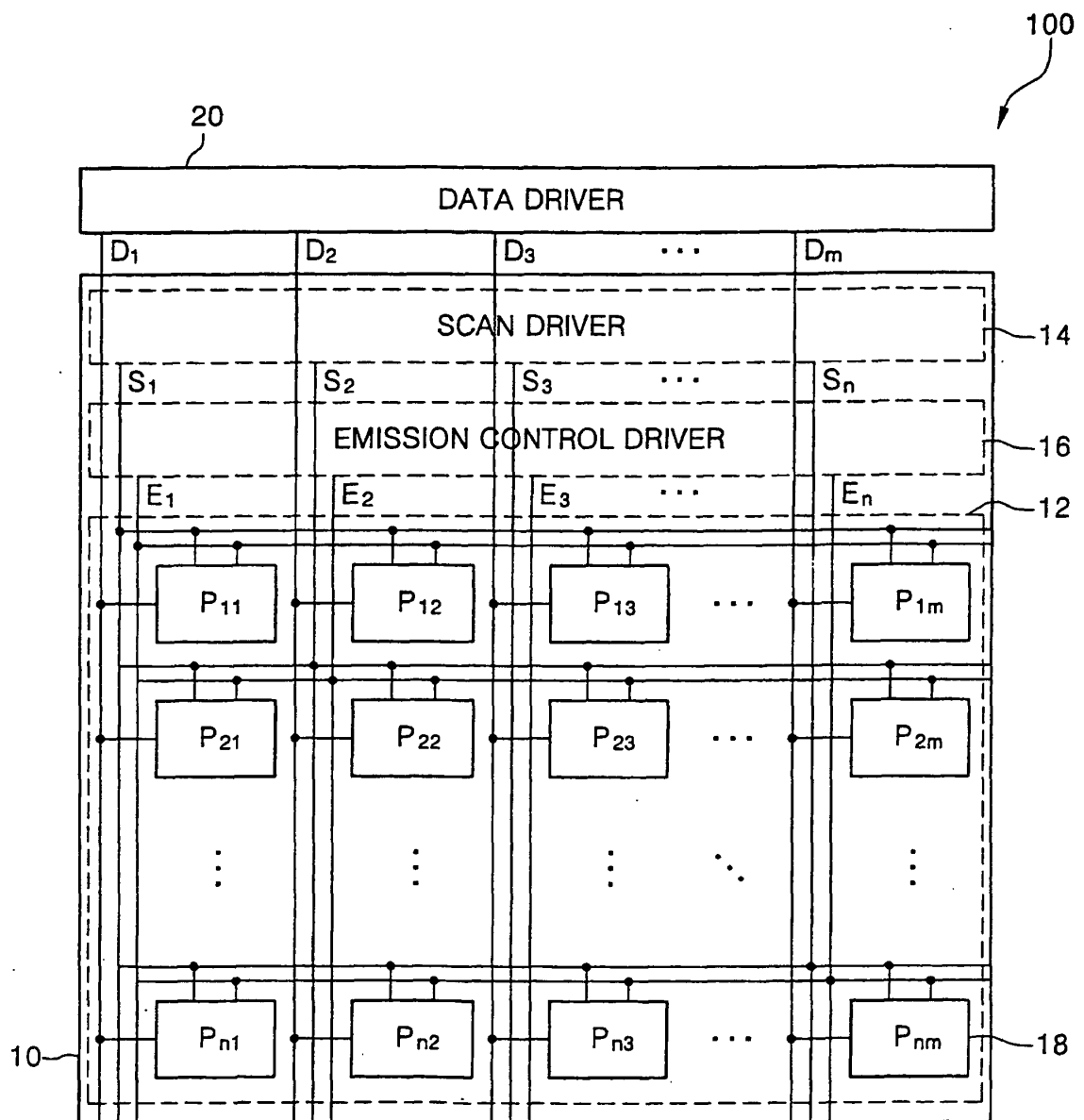


FIG. 3

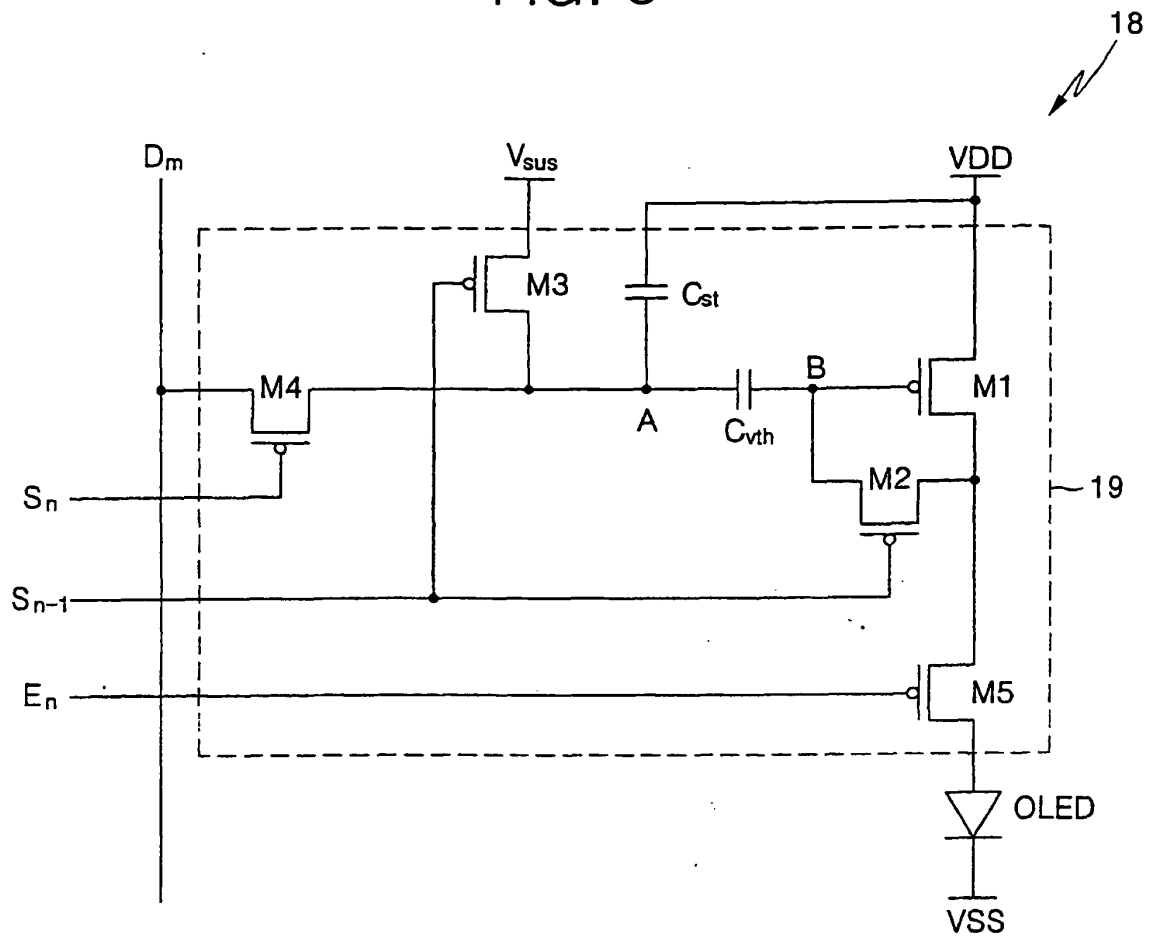


FIG. 4

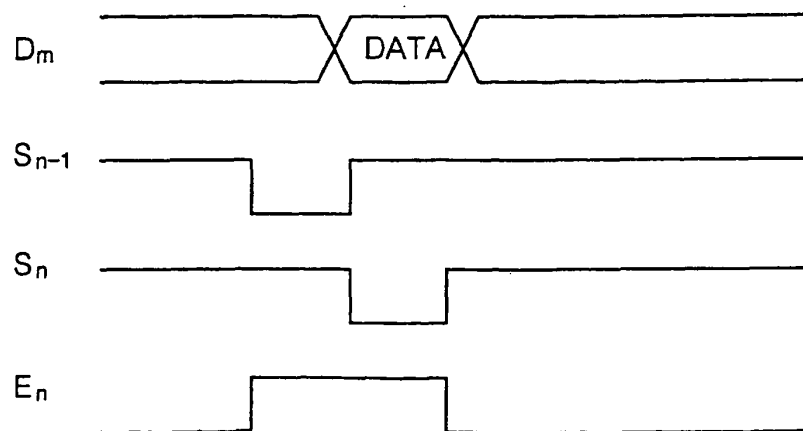


FIG. 5

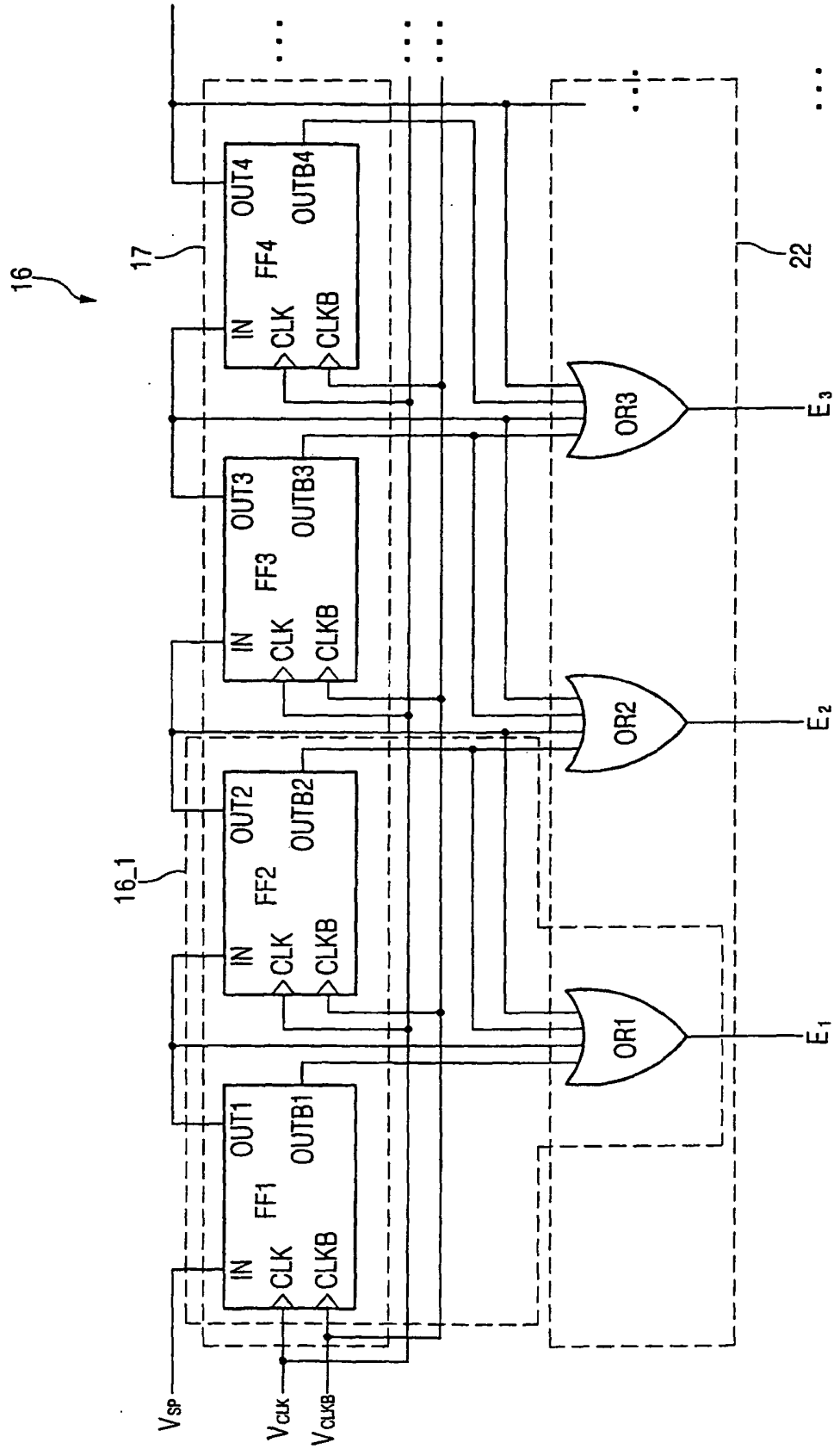


FIG. 6

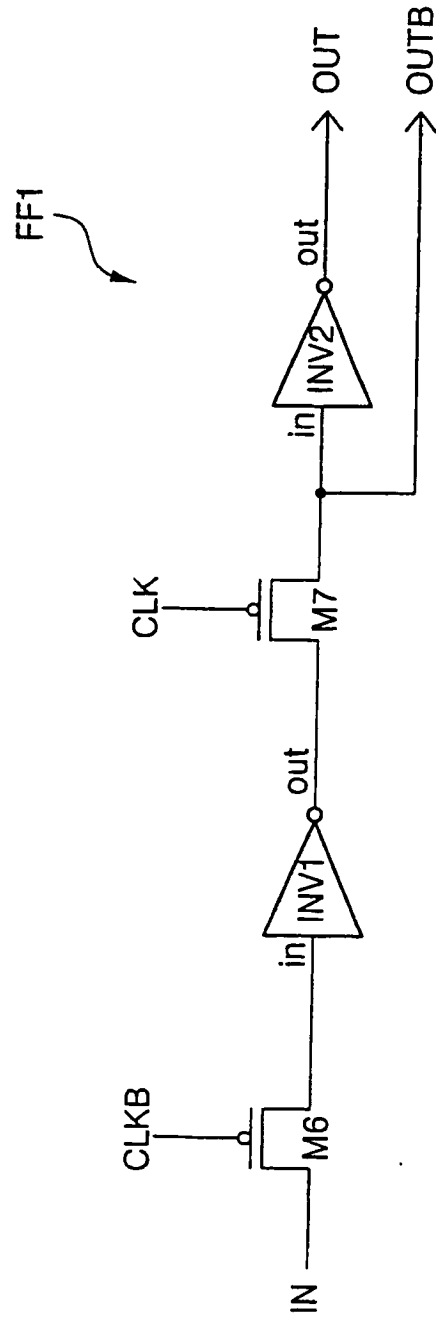


FIG. 7

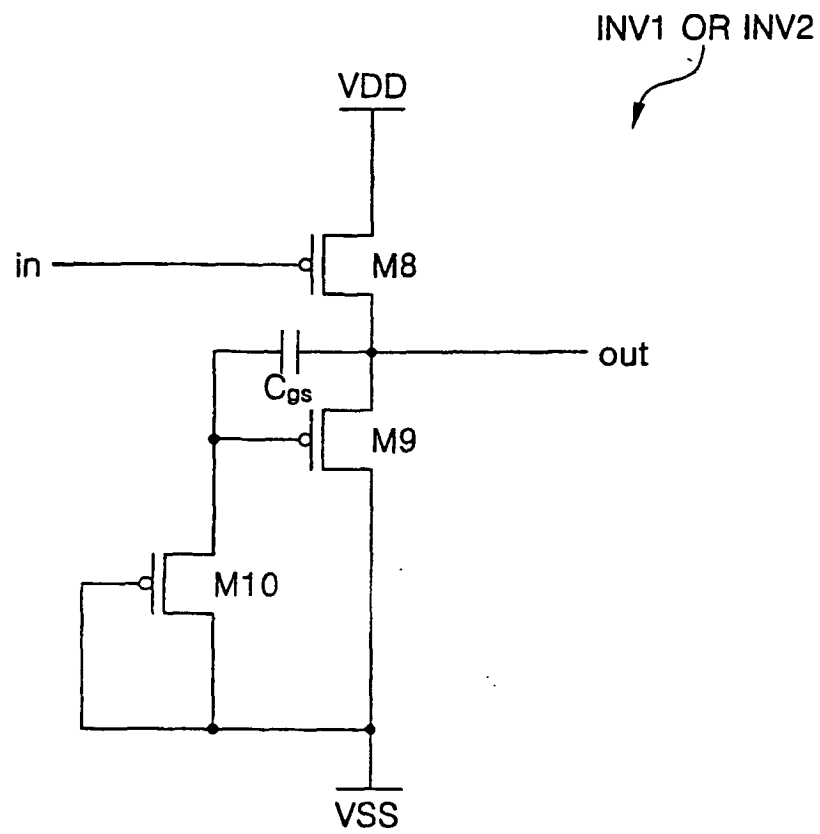


FIG. 8

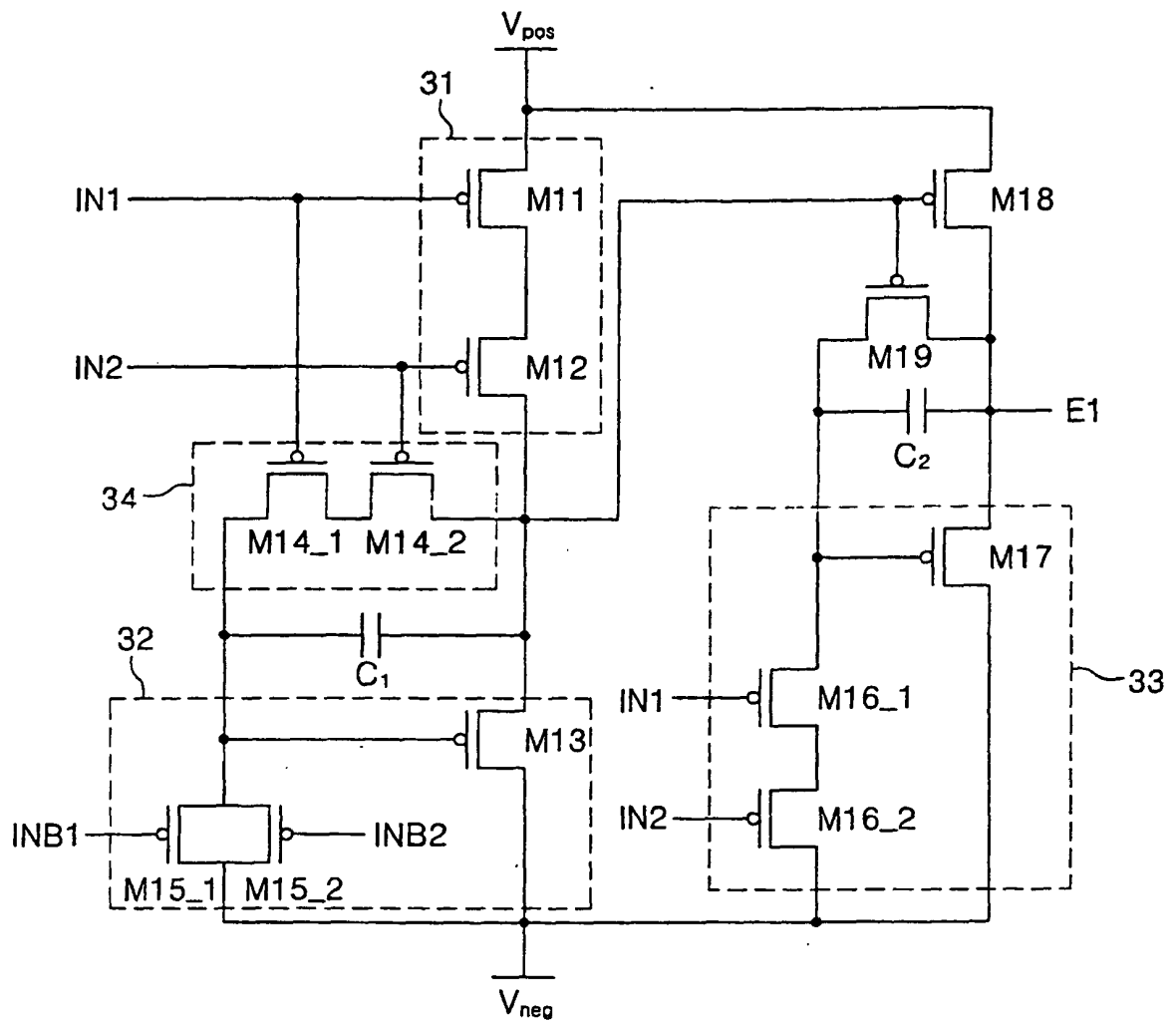
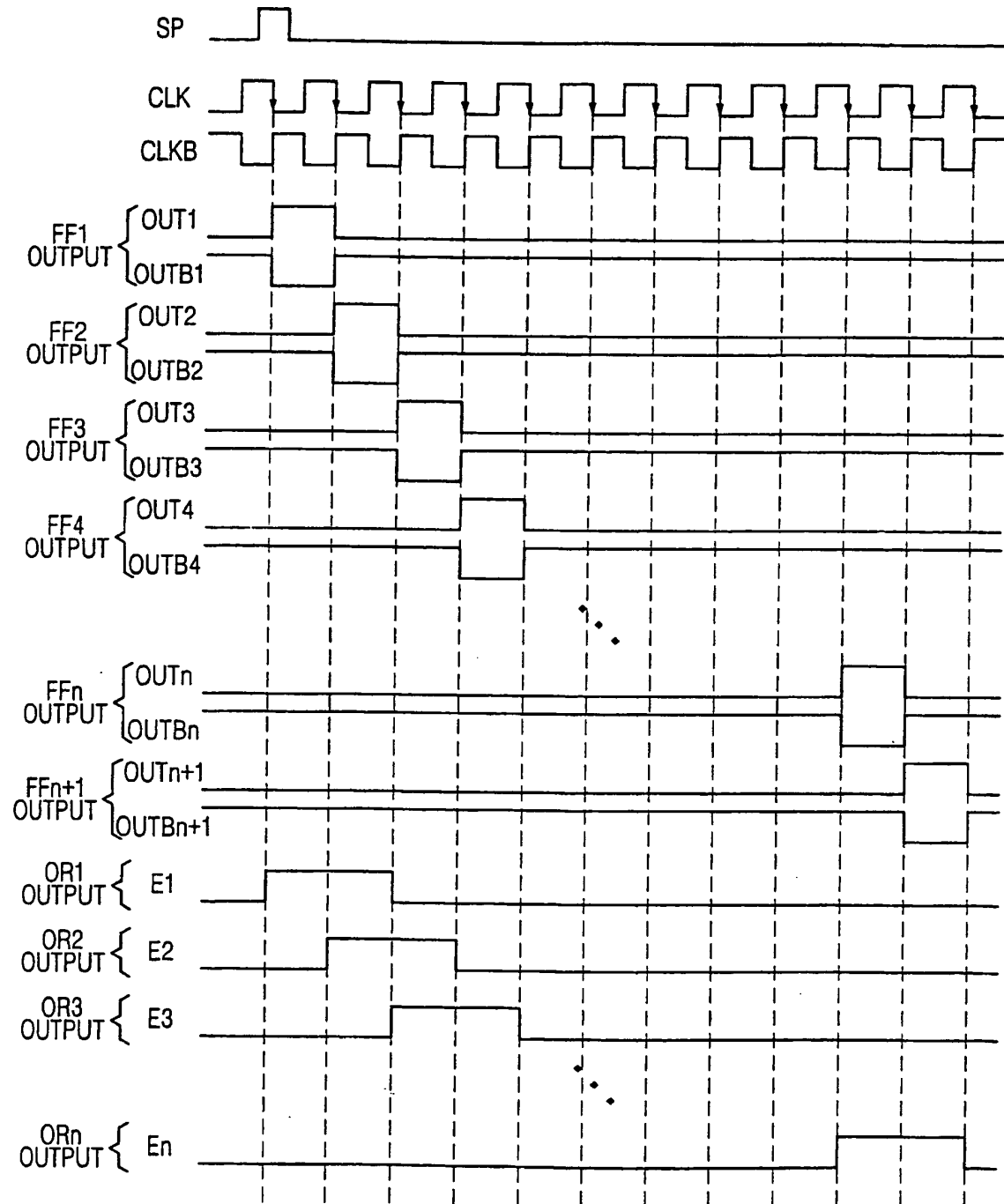


FIG. 9



专利名称(译)	有机发光显示装置，具有用于输出发射控制信号的发射控制驱动器		
公开(公告)号	EP1755103B1	公开(公告)日	2010-12-22
申请号	EP2006254019	申请日	2006-07-31
[标]申请(专利权)人(译)	三星斯笛爱股份有限公司		
申请(专利权)人(译)	三星SDI CO. , LTD.		
当前申请(专利权)人(译)	三星移动显示器有限公司.		
发明人	CHUNG, BO YONG LEGAL & IP TEAM CORP.PLANNING STAFF		
IPC分类号	G09G3/32		
CPC分类号	G09G3/3233 G09G3/3266 G09G2300/0408 G09G2300/0417 G09G2300/0819 G09G2300/0852 G09G2300/0861 G09G2310/0221 G09G2310/0262 G09G2330/021 G11C19/00 G11C19/184		
优先权	1020050075428 2005-08-17 KR 1020050075429 2005-08-17 KR		
其他公开文献	EP1755103A1		
外部链接	Espacenet		

摘要(译)

一种使用平铺技术的有机发光显示 (OLED) 装置，包括面板上系统 (SOP) 型发射控制驱动器。发射控制驱动器包括移位寄存器和具有多个逻辑门的逻辑运算部分，每个逻辑门接收来自移位寄存器的输出信号并对接收的信号执行逻辑或运算。使用两个相邻触发器的两个输出信号和两个反相输出信号来控制每个逻辑门的有效负载。而且，每个逻辑门对两个相邻触发器的两个输出信号执行逻辑“或”运算，并产生发射控制信号。触发器和发射控制驱动器的逻辑门包括正沟道金属氧化物半导体 (PMOS) 晶体管。

$$I_{\text{OLED}} = k(V_{\text{gs}} - |V_{\text{th}}|)^2 = k(V_{\text{DD}} - (V_{\text{DD}} - |V_{\text{th}}| - V_{\text{sws}} + V_{\text{data}}) - |V_{\text{th}}|)^2 \quad (1)$$

$$= k(V_{\text{data}} - V_{\text{sws}})^2,$$